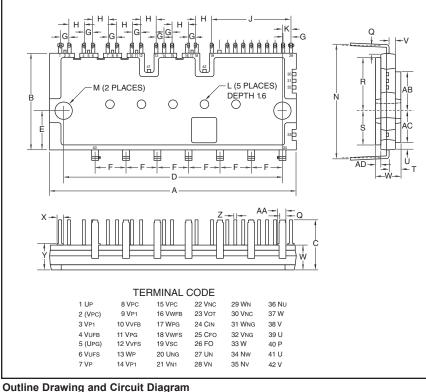


# **PS22A78-E**

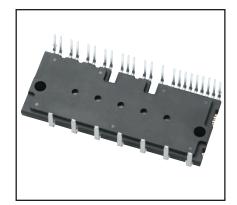
Powerex, Inc., 173 Pavilion Lane, Youngwood, Pennsylvania 15697 (724) 925-7272

# Intellimod<sup>™</sup> Module Dual-In-Line Intelligent **Power Module** 35 Amperes/1200 Volts



Dimensions	Inches	Millimeters
А	3.11±0.02	79.0±0.5
В	1.22±0.02	31.0±0.5
С	0.63	16.0
D	2.76±0.01	70.0±0.3
E	0.5	12.7
F	0.39±0.01	10.0±0.3
G	0.1±0.01	2.54±0.3
Н	0.2±0.01	5.08±0.3
J	1.0	25.4
K	0.11	2.8
L	0.12 Dia.	2.9 Dia.
М	0.18±0.01 Dia.	4.5±0.2 Dia.
Ν	1.42±0.02	36.2±0.5
Р	0.03	0.7

Dimensions	Inches	Millimeters
Q	0.08	2.0
R	0.66	16.73
S	0.44	11.13
Т	0.15±0.04	3.8±1.0
U	0.082	2.1
V	0.086	2.2
W	0.31	8.0
Х	0.07	1.8
Y	0.34	8.6
Z	0.03	0.8
AA	0.10	2.7
AB	0.48	12.33
AC	0.39	10.12
AD	0.068	1.75



# **Description:**

DIPIPMs are intelligent power modules that integrate power devices, drivers, and protection circuitry. Design time is reduced by the use of application-specific HVICs and value-added features such as linear temperature feedback. Overall efficiency and reliability are increased by the use of full gate CSTBT technology and low thermal impedance.

## Features:

- □ Low-loss, Full Gate **CSTBT IGBTs**
- □ Single Power Supply
- □ Integrated HVICs
- □ Direct Connection to CPU

# **Applications:**

- □ Variable Speed Pumps
- □ Variable Speed Compressors
- □ Small Motor Control

# **Ordering Information:**

PS22A78-E is a 1200V, 35 Ampere DIP Intelligent Power Module.



### PS22A78-E Intellimod™ Module Dual-In-Line Intelligent Power Module 35 Amperes/1200 Volts

# Absolute Maximum Ratings, $T_i = 25^{\circ}C$ unless otherwise specified

Characteristics	Symbol	PS22A78-E	Units
Self-protection Supply Voltage Limit (Short Circuit Protection Capability)*	V <sub>CC(prot.)</sub>	800	Volts
Module Case Operation Temperature (See T <sub>C</sub> Measurement Point Below)	т <sub>С</sub>	-20 to 100	°C
Storage Temperature	T <sub>stg</sub>	-40 to 125	°C
Mounting Torque, M4 Mounting Screws	_	13	in-lb
Module Weight (Typical)	_	65	Grams
Isolation Voltage, AC 1 minute, 60Hz Sinusoidal, Connection Pins to Heatsink Plate	V <sub>ISO</sub>	2500	Volts

## **IGBT Inverter Sector**

Supply Voltage (Applied between P-NU, NV, NW)	V <sub>CC</sub>	900	Volts
Supply Voltage, Surge (Applied between P-NU, NV, NW)	V <sub>CC(surge)</sub>	1000	Volts
Collector-Emitter Voltage (T <sub>C</sub> = 25°C)	V <sub>CES</sub>	1200	Volts
Collector Current ( $T_C = 25^{\circ}C$ )	±ΙC	35	Amperes
Peak Collector Current (T <sub>C</sub> = 25°C, <1ms)	±ICP	70	Amperes
Collector Dissipation (T <sub>C</sub> = 25°C, per 1 Chip)	PC	129.9	Watts
Power Device Junction Temperature**	Тj	-20 to 150	°C

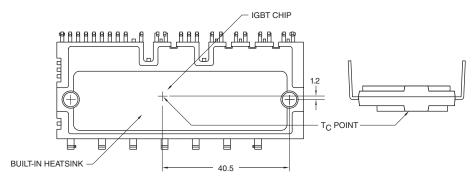
## **Control Sector**

Supply Voltage (Applied between VP1-VPC, VN1-VNC)	VD	20	Volts
Supply Voltage (Applied between VUFB-VUFS, VVFB-VVFS, VWFB-VWFS)	V <sub>DB</sub>	20	Volts
Input Voltage (Applied between U <sub>P</sub> , V <sub>P</sub> , W <sub>P</sub> -V <sub>PC</sub> , U <sub>N</sub> , V <sub>N</sub> , W <sub>N</sub> -V <sub>NC</sub> )	V <sub>IN</sub>	-0.5 ~ V <sub>D</sub> +0.5	Volts
Fault Output Supply Voltage (Applied between F <sub>O</sub> -V <sub>NC</sub> )	V <sub>FO</sub>	-0.5 ~ V <sub>D</sub> +0.5	Volts
Fault Output Current (Sink Current at F <sub>O</sub> Terminal)	I <sub>FO</sub>	1	mA
Current Sensing Input Voltage (Applied between CIN-VNC)	V <sub>SC</sub>	-0.5 ~ V <sub>D</sub> +0.5	Volts

\*V<sub>D</sub> = 13.5 ~ 16.5V, Inverter Part, T<sub>i</sub> = 125°C, Non-repetitive, Less than 2μs

\*\*The maximum junction temperature rating of the power chips integrated within the DIPIPM is 150°C (@T<sub>f</sub>  $\leq$  100°C). However, to ensure safe operation of the DIPIPM, the average junction temperature should be limited to T<sub>j(avg)</sub>  $\leq$  125°C (@T<sub>f</sub>  $\leq$  100°C).

# T<sub>C</sub> Measurement Point





## PS22A78-E

Intellimod™ Module Dual-In-Line Intelligent Power Module 35 Amperes/1200 Volts

# Electrical and Mechanical Characteristics, $T_i = 25^{\circ}C$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Тур.	Max.	Units
IGBT Inverter Sector						
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_{C}$ = 35A, $T_{j}$ = 25°C, $V_{D}$ = $V_{DB}$ = 15V, $V_{IN}$ = 5V	_	1.9	2.6	Volts
		$I_{C}$ = 35A, $T_{j}$ = 125°C, $V_{D}$ = $V_{DB}$ = 15V, $V_{IN}$ = 5V	_	2.0	2.7	Volts
Diode Forward Voltage	V <sub>EC</sub>	T <sub>j</sub> = 25°C, -I <sub>C</sub> = 35A, V <sub>IN</sub> = 0V	_	2.8	3.3	Volts
Inductive Load Switching Times	t <sub>on</sub>		0.8	1.5	2.2	μs
	t <sub>rr</sub>	V <sub>CC</sub> = 600V, V <sub>D</sub> = V <sub>DB</sub> = 15V,		0.3		μs
	t <sub>C(on)</sub>	$I_{C}$ = 35A, $T_{j}$ = 125°C, $V_{IN}$ = 0 $\Leftrightarrow$ 5V,	_	0.6	0.9	μs
	toff	Inductive Load (Upper-Lower Arm)	_	2.8	3.8	μs
	t <sub>C(off)</sub>		_	0.7	1.0	μs
Collector-Emitter Cutoff Current	ICES	$V_{CE} = V_{CES}, T_j = 25^{\circ}C$	_	_	1.0	mA
		$V_{CE} = V_{CES}, T_j = 125^{\circ}C$	_	_	10	mA
Control Sector						
Circuit Current	ID	V <sub>D</sub> = V <sub>DB</sub> = 15V, V <sub>IN</sub> = 5V,	_	_	3.70	mA
	D	Total of V <sub>P1</sub> -V <sub>PC</sub> , V <sub>N1</sub> -V <sub>NC</sub>				
		$V_{\rm D} = V_{\rm DB} = 15V, V_{\rm IN} = 5V,$		_	1.30	mA
		VUFB-VUFS, VVFB-VVFS, VWFB-VWFS				
		$V_{\rm D} = V_{\rm DB} = 15V, V_{\rm IN} = 0V,$	_	_	3.50	mA
		Total of V <sub>P1</sub> -V <sub>PC</sub> , V <sub>N1</sub> -V <sub>NC</sub>				
		$V_{\rm D} = V_{\rm DB} = 15$ V, $V_{\rm IN} = 0$ V,	_	_	1.30	mA
		VUFB-VUFS, VVFB-VVFS, VWFB-VWFS				
Fault Output Voltage	V <sub>FOH</sub>	$V_{SC} = 0V, F_O$ Terminal Pull-up to 5V by $10k\Omega$	4.9	_		Volts
	V <sub>FOL</sub>	V <sub>SC</sub> = 1V, I <sub>FO</sub> = 1mA	_	_	1.1	Volts
Input Current	I <sub>IN</sub>	V <sub>IN</sub> = 5V	0.7	1.5	2.0	mA
Short-Circuit Trip Level*	I <sub>SC</sub>	$-20^{\circ}C \le T_{C} \le 100^{\circ}C, V_{D} = 15V$	59.5	_		Amps
Supply Circuit Undervoltage	UV <sub>DBt</sub>	Trip Level, T <sub>C</sub> ≤ 100°C	10.0	_	12.0	Volts
Protection	UV <sub>DBr</sub>	Reset Level, T <sub>C</sub> ≤ 100°C	10.5	_	12.5	Volts
	UV <sub>Dt</sub>	Trip Level, T <sub>C</sub> ≤ 100°C	10.3	_	12.5	Volts
	UV <sub>Dr</sub>	Reset Level, T <sub>C</sub> ≤ 100°C	10.8	_	13.0	Volts
Fault Output Pulse Width**	t <sub>FO</sub>	C <sub>FO</sub> = 22nF	1.6	2.4		ms
ON Threshold Voltage	V <sub>th(on)</sub>	Applied between UP, VP, WP-VPC,		_	3.5	Volts
OFF Threshold Voltage	V <sub>th(off)</sub>	U <sub>N</sub> , V <sub>N</sub> , W <sub>N</sub> -V <sub>NC</sub>	0.8	_		Volts
Temperature Output***	V <sub>OT</sub>	At LVIC Temperature = 85°C	3.50	3.63	3.76	Volts

\* Short-Circuit protection is functioning only at the lower arms. Please select the value of the external shunt resistor such that the SC trip level is less than 85A.

\*\*Fault signal is asserted when the lower arm short circuit or control supply under-voltage protective functions operate. The fault output pulse-width tFO depends on the capacitance value of C<sub>FO</sub> according to the following approximate equation:  $C_{FO} = (12.2 \times 10^{-6} \times t_{FO} [F])$ . \*\*\*When the temperature rises excessively, the controller (MCU) should stop the DIPIPM.



### PS22A78-E Intellimod™ Module Dual-In-Line Intelligent Power Module 35 Amperes/1200 Volts

# Thermal Characteristics, $T_i = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Units
Thermal Resistance Junction to Case	R <sub>th(j-C)Q</sub>	IGBT Part (Per 1/6 Module)	_	_	0.77	°C/Watt
Thermal Resistance Junction to Case	R <sub>th(j-C)D</sub>	FWDi Part (Per 1/6 Module)	—	—	1.25	°C/Watt

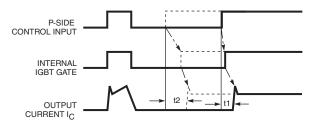
## **Recommended Conditions for Use**

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Units
Supply Voltage	V <sub>CC</sub>	Applied between P-NU, NV, NW	350	600	800	Volts
Control Supply Voltage	VD	Applied between VP1-VPC, VN1-VNC	13.5	15.0	16.5	Volts
	V <sub>DB</sub>	Applied between VUFB-VUFS,	13.0	15.0	18.5	Volts
		VVFB-VVFS, VWFB-VWFS				
Control Supply Variation	$\Delta V_D, \Delta V_{DB}$		-1	_	1	V/µs
Arm Shoot-through	<sup>t</sup> DEAD	For Each Input Signal, T <sub>C</sub> ≤ 100°C	3.3	_		μs
Blocking Time						
PWM Input Frequency	fPWM	T <sub>C</sub> ≤ 100°C, T <sub>j</sub> ≤ 125°C	_	_	15	kHz
Allowable rms Current*	Ι <sub>Ο</sub>	V <sub>CC</sub> = 600V, V <sub>D</sub> = 15V,	_	_	12.8	Arms
		f <sub>C</sub> = 15kHz, PF = 0.8, Sinusoidal PWM,				
		T <sub>j</sub> ≤ 125°C, T <sub>C</sub> ≤ 100°C				
Minimum Input	P <sub>WIN(on)</sub> **		_	_	_	μs
Pulse Width	P <sub>WIN(off)***</sub>					
	$I_{\rm C} \le 35 {\rm A}$	$350 \le V_{CC} \le 800V$ , $13.5 \le V_{D} \le 16.5V$ ,	_	_	_	μs
	35 ≤ I <sub>C</sub> ≤ 59.5A	 13.5 ≤ V <sub>DB</sub> ≤ 16.5V, -20°C ≤ T <sub>C</sub> ≤ 100°C,	_	_		μs
		N-line Wiring Inductance Less Than 10nH				
V <sub>NC</sub> Variation	V <sub>NC</sub>	Between V <sub>NC</sub> -NU, NV, NW (Including Surge)	-5.0	_	5.0	Volts

\* The allowable rms current value depends on the actual application conditions.

\*\*If input signal ON pulse is less than P<sub>WIN(on)</sub>, the device may not respond. \*\*\*The IPM may fail to respond to an ON pulse if the preceeding OFF pulse is less than P<sub>WIN(off)</sub>.

# Delayed Response Against Shorter Input OFF Signal Than PWIN(off), P-side only



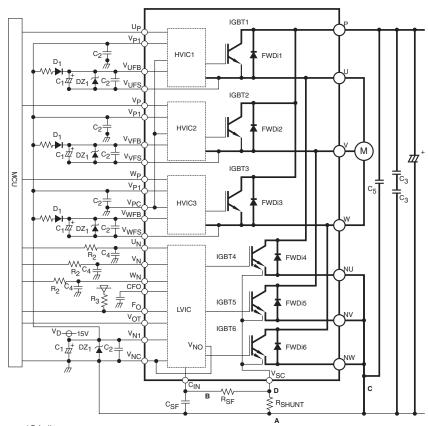
Solid Line – OFF Pulse Width >  $P_{WIN(off)}$ : Turn ON time t1. Dotted Line - OFF Pulse Width < PWIN(off): Turn ON time t2.



### PS22A78-E

Intellimod<sup>™</sup> Module **Dual-In-Line Intelligent Power Module** 35 Amperes/1200 Volts

## **Application Circuit**



mpone	int Selection:	
gn.	Typ. Value	Description
	1A, 600V	Control and boot
1	24V, 1W	Control and boot
	10-100µF, 50V	Boot strap supply
	0.22-2.0µF, 50V	Local decoupling
	200 to 2500µF, 450V	Main DC bus filte
	100pF, 50V	Optional input sig
	0.1-0.22µF, 1000V	Surge voltage su
F	1000pF, 50V	Short circuit dete
E	1.8kO	Short circuit dete

Dsgn.	Typ. Value	Description
D <sub>1</sub>	1A, 600V	Control and boot strap supply overvoltage suppression
DZ <sub>1</sub>	24V, 1W	Control and boot strap supply over voltage suppression
C <sub>1</sub>	10-100µF, 50V	Boot strap supply reservoir – electrolytic long lifem low impedance, 105°C
C <sub>2</sub>	0.22-2.0µF, 50V	Local decoupling/High frequency noise filters – multilayer ceramic (Note 4)
C <sub>3</sub>	200 to 2500µF, 450V	Main DC bus filter capacitor – electrolytic, long life, high ripple current, 105°C
C <sub>4</sub>	100pF, 50V	Optional input signal noise filter – multilayer ceramic (Note 11)
C <sub>5</sub>	0.1-0.22µF, 1000V	Surge voltage suppression (Note 2)
CSF	1000pF, 50V	Short circuit detection filter capacitor – multilayer ceramic
RSF	1.8kΩ	Short circuit detection filter resistor
RSHUNT	20ohm-500ohm	Current sensing resistor
R <sub>1</sub>	1-10Ω	Boot strap supply inrush limiting resistor - non-inductive, temperature stable, tight tolerance (Note 5)
R <sub>2</sub>	330Ω	Optional input signal noise filter (Note 11)
R <sub>3</sub>	10kΩ	Fault signal pull-up resistor (Note 9)

Notes

Cor

1) If control GND is connected to power GND by broad pattern, it may cause malfunction by power GND fluctuation.

- It is recommended to connect control GND at only a point at which NU, NV, NW are connected to power GND line. 2)
- To prevent surge destruction, the wiring between the smoothing capacitor and the P-N1 terminals should be as short as possible. Generally inserting a  $0.1\mu 0.22\mu$ F snubber capacitor C<sub>3</sub> between the P-N1 terminals is recommended. 3)
- The time constant  $R_1, C_4$  of RC filter for preventing the protection circuit malfunction should be selected in the range of 1.5 $\mu$  ~ 2 $\mu$ s. SC interrupting time might vary with the wiring pattern. Tight tolerance, temp-compensated type is recommended for  $R_1, C_4$ . All capacitors should be mounted as close to the terminals of the DIPIPM as possible. (C1: good temperature, frequency 4)

characteristics electrolytic type, and C<sub>2</sub>: good temperature, frequency and DC bias characteristic ceramic type are recommended.) It is recommended to insert a Zener diode DZ<sub>1</sub> (24V/1W) between each pair of control supply terminals to prevent surge destruction. 5)

- 6)
- To prevent erroneous SC protection, the wiring from  $V_{SC}$  terminals to  $C_{IN}$  filter should be divided at the point D that is close to the terminal of sense resistor and the wiring should be patterned as short as possible. For sense resistor, the variation within 1% (including temperature characteristics), low inductance type is recommended. 7)
- 1/8W is recommended, but an evaluation of your system is recommended. To prevent erroneous operation, wiring A, B, and C should be as short as possible. 8)

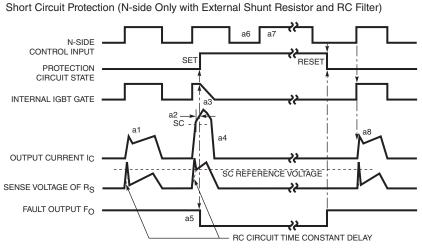
b) To prevent environments operation, ming P, B, and C shall be as allowing be as allowing by the prevent environments of the prevent environments of the prevent environment environment of the prevent environment envinter environment environment environment environment environ

should be patterned as short as possible. When inserting the RC filter, make sure the input signal level meets the turn-on and turn-off threshold voltage. Thanks to HVIC inside the module, connection to the MCU may be direct or with an opto-coupler.



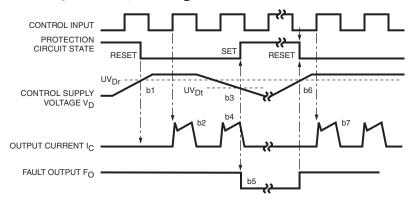
PS22A78-E Intellimod<sup>™</sup> Module Dual-In-Line Intelligent Power Module 35 Amperes/1200 Volts

# **Protection Function Timing Diagrams**



- a1: Normal operation IGBT turns on and carries current.
- a2: Short circuit current is detected (SC trigger).
- a3: All N-side IGBT's gate are hard interrupted.
- a4: All N-side IGBT's turn off.
- a5:  $\rm F_O$  output wirh a fixed pulse width (determined by the external capacitance  $\rm C_{FO}).$
- a6: Input "L" IGBT off.
- a7: Input "H" IGBT on, but during the  $F_O$  output perid the IGBT will not turn on.
- a8: IGBT turns on when L $\rightarrow$ H signal is input after F<sub>O</sub> is reset.

Under-Voltage Protection (N-side , UVD)



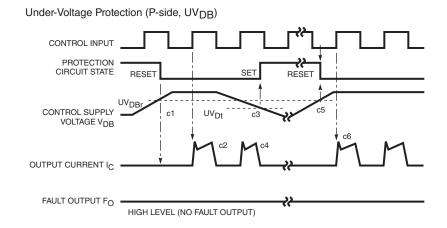
- b1: Control supply voltage V<sub>D</sub> rises After V<sub>D</sub> level reaches under voltage reset level (UV<sub>Dr</sub>), the circuits start to operate when next input is applied.
- b2 : Normal operation IGBT turns on and carries current.
- b3: V<sub>D</sub> level dips to under voltage trip level (UV<sub>Dt</sub>).
- b4: All N-side IGBT's turn off in spite of control input condition.
- b5: F<sub>O</sub> is low for a minimum period determined by the capacitance C<sub>FO</sub> but continuously during UV period.
- b6: V<sub>D</sub> level reaches UV<sub>Dr</sub>.
- b7: Normal operation IGBT turns on and carries current.



## PS22A78-E

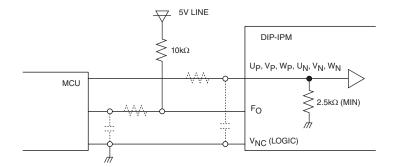
Intellimod<sup>™</sup> Module Dual-In-Line Intelligent Power Module 35 Amperes/1200 Volts

## **Protection Function Timing Diagrams**



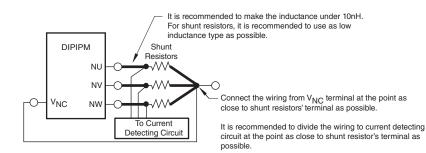
- c1: Control supply voltage V\_{DB} rises After V\_{DB} level reaches under voltage reset level (UV\_{DBr}),
- the circuits starts to operate when next input is applied. c2: Normal operation – IGBT turns on and carries current.
- c2: Normal operation IGBT turns on and carries curres
  c3: V<sub>DB</sub> level dips to under voltage trip level (UV<sub>DBt</sub>).
- c4: P-side IGBT turns off in spite of control input signal level, but there is no F<sub>O</sub> signal output.
- c5: V<sub>DB</sub> level reaches UV<sub>DBr</sub>.
- c6: Normal operation IGBT on and carries current.

## **Typical Interface Circuit**



NOTE: RC coupling at each input (parts shown dotted) may change depending on the PWM control scheme used in the application and the wiring impedance of the printed circuit board. The DIPIPM input signal section integrates a 2.5kΩ (min) pull-down resistor. Therefore, when using an external filtering resistor, care must be taken to satisfy the turn-on threshold voltage requirement.

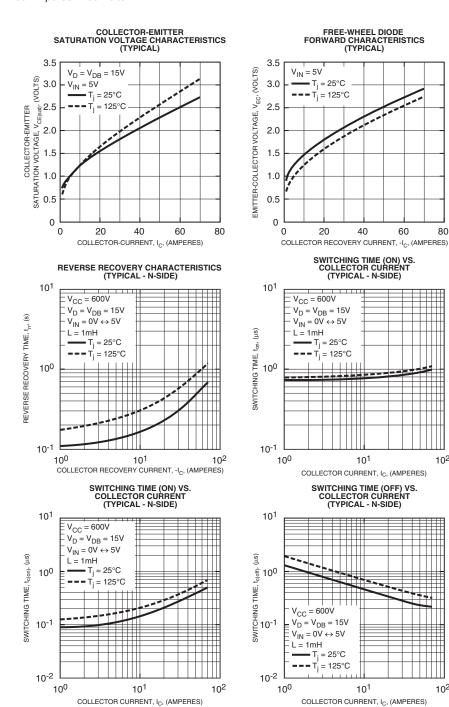
## Wiring Method Around Shunt Resistor

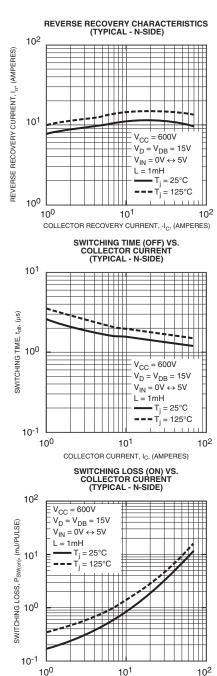




#### PS22A78-E

Intellimod™ Module **Dual-In-Line Intelligent Power Module** 35 Amperes/1200 Volts





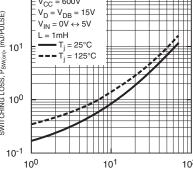
60

80

10<sup>2</sup>

10<sup>2</sup>

10<sup>1</sup> COLLECTOR CURRENT, IC, (AMPERES)





### PS22A78-E

Intellimod<sup>™</sup> Module Dual-In-Line Intelligent Power Module 35 Amperes/1200 Volts

